

isc Silicon NPN Power Transistor

MJH16006

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 450V(\text{Min})$
- High Switching Speed

APPLICATIONS

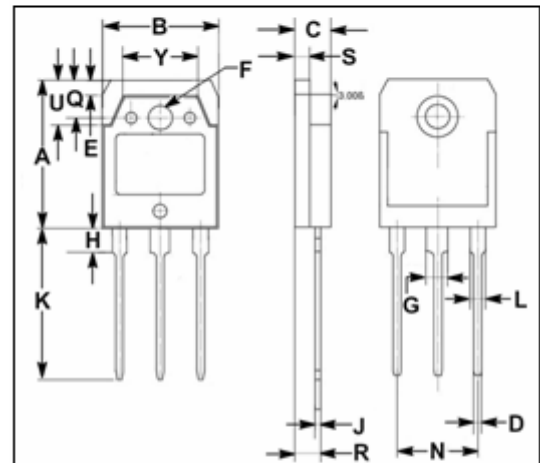
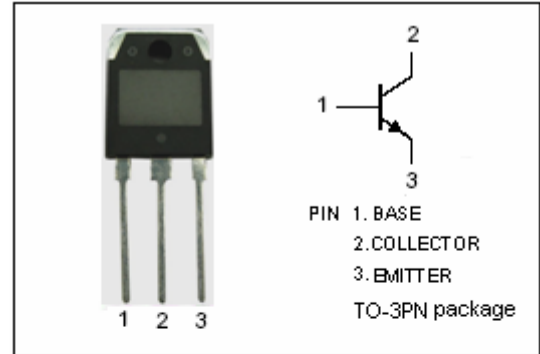
- Designed for high-voltage ,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switch-mode applications.
Typical applications:
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	850	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	16	A
I_B	Base Current-Continuous	6	A
I_{BM}	Base Current-Peak	12	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	125	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}$; $I_B=0$	450			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}$; $I_B=0.4\text{A}$			2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}$; $I_B=0.66\text{A}$ $I_C=5\text{A}$; $I_B=0.66\text{A}$, $T_C=100^{\circ}\text{C}$			3.0 3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}$; $I_B=0.66\text{A}$ $I_C=5\text{A}$; $I_B=0.66\text{A}$, $T_C=100^{\circ}\text{C}$			1.5 1.5	V
I_{CEV}	Collector Cutoff Current	$V_{CEV}=850\text{V}$; $V_{BE(off)}=1.5\text{V}$ $V_{CEV}=850\text{V}$; $V_{BE(off)}=1.5\text{V}$; $T_C=100^{\circ}\text{C}$			0.25 1.5	mA
I_{CER}	Collector Cutoff Current	$V_{CE}=850\text{V}$; $R_{BE}=50\Omega$; $T_C=100^{\circ}\text{C}$			2.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}$; $I_C=0$			1.0	mA
h_{FE}	DC Current Gain	$I_C=8\text{A}$; $V_{CE}=5\text{V}$	5			
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=10\text{V}$; $f_{test}=1.0\text{kHz}$			350	pF

Switching times;Resistive Load

t_d	Delay Time	$I_C=5\text{A}$, $V_{CC}=250\text{V}$; $R_{B2}=4\Omega$; $I_{B1}=0.66\text{A}$; $I_{B2}=-1.3\text{A}$; $PW=30\mu\text{s}$; Duty Cycle $\leq 2.0\%$		20	50	ns
t_r	Rise Time			85	250	ns
t_s	Storage Time			1000	2500	ns
t_f	Fall Time			70	250	ns